Heat conduction in one dim ensional systems: Fourier law, chaos, and heat control

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1 Introduction

It seems there is no problem in modern physics for which there are on record as many false starts, and as many theories which overlook some essential feature, as in the problem of the thermal conductivity of nonconducting crystals" [1]. This statement by R. Peierls goes back to almost 50 years ago, yet it appears to be still valid. Compared with charge ow (electric current), much less is known about the heat ow.

Nevertheless, encouraging results have been obtained in recent years (see reviews[2] and the references therein). For example it is now known that in one dim ensional systems of the Ferm i-Pasta-Ulam (FPU) type β], heat conduction is anom alous and the coe cient of therm al conductivity diverges L²⁼⁵ (when the transverse motion is conwith the system size L as L¹⁼³ [4]). The connection between anomalous conductivity and anom alous di usion has been also established [5, 6], which implies in particular that a subdi usive system is an insulator in the therm odynam ic lim it and a ballistic system is a perfect them al conductor, the Fourier law being therefore valid only when phonons undergo a normal di usive motion. M ore profoundly, it has been claried that exponential dynamical instability is a su cient[7, 8] but not a necessary condition for the validity of Fourier law [9, 10, 11, 12]. These basic studies not only enrich our know ledge of the fundam ental transport laws in statistical mechanics, but also open the way for applications such as designing novel them alm aterials and/or devices such as the therm alrecti er[13, 14] and the therm altransistor[15].

In this paper we give a brief review of the relation between m icroscopic dynam ical properties and the Fourier law of heat conduction as well as the connection between anom alous conduction and anom alous di usion. We then discuss the possibility to control the heat ow.

2 M icroscopic dynam ics and the Fourier heat law

In spite of several years of investigation, so far there is neither phenom enological nor fundam ental transport theory which can predict whether or not a given classical, many-body Hamiltonian system, yields an energy transport governed by the Fourier heat law. It is known that heat ow obeys a simple di usion equation which can be regarded as the continuum limit of a discrete random walk. However, modern ergodic theory tells us that for K-systems, a sequence of measurements with nite precision minics a truly random sequence and therefore these systems appear precisely those deterministically random systems tacitly required by transport theory. It is therefore interesting to establish which class, if any, of many-body systems satisfy the necessary stringent requirements for the validity of Fourier law of heat conduction.

$2.1\ \mathrm{D}$ ynam ical chaos is a su cient condition for the Fourier law

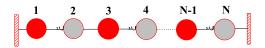
D ing-a-ling m odel

The rst example for which convincing evidence has been provided that Fourier law can be derived on purely dynamical grounds, without any additional statistical assumptions, is the so-called ding-a-ling model proposed in [7].

The Ham iltonian of the ding-a-ling model is:

$$H = \frac{1}{2}^{X}$$
 $p_{k}^{2} + !_{k}^{2}q_{k}^{2} + \text{hard point core}$ (1)

where $!_k$ equals ! for even k and zero for odd k and where all particles have unit mass. It can be shown that it is possible to x the energy per particle (E = 1) and the half of the lattice distance between two bound particles (l_0 = 1). A fler this the dynam ics is uniquely determined by the frequency ! which becomes therefore the only adjustable parameter.



F ig. 1. The N-particle ding-a-ling m odel. 0 dd particles can m ove freely in between two collisions, while even particles are bounded by a harm onic spring.

As it seen in Fig 1. the model is a one-dimensional array of equal mass, hard-point particles, the even-numbered particles form a set of equally spaced harm onic oscillators with each oscillator bound to its individual lattice site

and with all oscillators vibrating with the same frequency !. The oddnumbered particles are free particles constrained only by the two adjacent even-numbered oscillators.

This model has been chosen in order to meet two requirements. First, it is necessary to select a determ inistically random system, and second, the system must be su ciently simple to allow e cient numerical analysis. Let us also recall that even systems obeying the Fourier heat law can transport energy in the form of slow ly decaying coherent excitations such as soundlike pulses. In num erical experim ents, which unavoidably consider only a small number of particles, this phenomenon is quite troublesome. Though K or alm ost K-system quarantees that these soundlike solutions will eventually decay, one needs to nd a small chaotic system in which this decay rate is su ciently rapid[16]. The selected model (1) is a many-body system which exhibits, as the frequency is varied, the full range of behaviour from integrable to almost K and which at the same time has no problem with energy-bearing, long-lived, solitonlike pulses. Indeed, it can be shown that as! is increased from zero (which is the well known integrable 1-d hard point gas), the system undergoes a transition from integrable to almost fully chaotic. This fact makes this model ideal to study the connection between Fourier law and microscopic dynam ical chaos.

Heat conductivity has been studied by placing the end particles in contact with two thermal reservoirs at dierent temperatures (see [7] for details) and then integrating the equations of motion. Numerical results [7] demonstrated that, in the small! regime, the heat conductivity is system size dependent, while at large!, when the system becomes almost fully chaotic, the heat conductivity becomes independent of the system size (if the size is large enough). This means that Fourier law is obeyed in the chaotic regime.

Lorentz gas channel

The above conclusions have been nicely con med and clari ed in [8] where the heat conduction has been studied in a Lorentz gas channel – a quasi one dimensional billiard with circular scatterers. The model (see Fig. 2) consists of two parallel lines and a series of semicircles of radius R placed in a triangular lattice along the channel. By construction no particle can move along the horizontal direction without colliding with the disks. The dynam – ics in the Lorentz gas is rigorously known to be mixing and all trajectories with nonzero projection on the horizontal direction are of hyperbolic type; further it has positive Kolmogorov-Sinai entropy and a well de ned di usive behavior. Very accurate numerical evidence has been provided [8] which shows that heat conduction in this model obeys the Fourier law. This result therefore clearly indicates that mixing with positive Lyapounov exponents is a su cient condition to ensure Fourier law of heat conduction.



F ig. 2. The geom etry of the Lorentz gas channel m odel. The two heat reservoirs at tem peratures $T_{\rm L}$ and $T_{\rm R}$ are indicated.

2.2 Chaos is not a necessary condition

Triangle billiard gas channel

Quite naturally, the next question which arises is whether strong, exponential unstable chaos, being su cient, is also necessary.

In this connection let us remark that in spite of severale orts, the relation between Lyapounov exponents, correlations decay, di usive and transport properties is still not completely clear. For example a model has been presented [17] which has zero Lyapounov exponent and yet it exhibits unbounded Gaussian di usive behavior. Since di usive behavior is at the root of normal heat transport then the above result [17] constitutes a strong suggestion that normal heat conduction can take place even without the strong requirement of exponential instability.

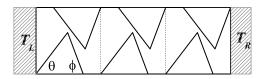


Fig. 3. The geometry of the triangle billiard gas channel Particles m ove in the region outside the triangular scatterers. The two heat reservoirs at temperatures $T_{\rm L}$ and $T_{\rm R}$ are indicated.

The above problem has been addressed in [11], where we have considered a quasi-one dimensional billiard model which consists of two parallel lines and a series of triangular scatterers (see Fig.3). In this geometry, no particle can move between the two reservoirs without su ering elastic collisions with the triangles. Therefore this model is analogous to the previous Lorentz gas channel with triangles instead of discs: the essential dierence is that in the triangular model the dynamical instability is linear and therefore the Lyapounov exponent is zero.

Strong numerical evidence has been given [18] that the motion inside a triangular billiard, with all angles irrational with is mixing, without

any time scale. It is therefore reasonable to expect that the motion inside the irrational polygonal area of Fig 3 is disusive thus leading to normal conductivity.

Indeed, num erical results in [11] show that in the irrational case (when the ratio = and = are irrational num bers) the system in Fig 3 exhibits norm aldi usion and the heat conduction obeys the Fourier law. In the rational case instead, the system shows a superdi usive behavior, $h^2i = 2D t^{1:178}$ [11] and the heat conductivity diverges with the system size as $N^{0:25}$ 0:01.

A lternate m ass-core hard potential channel

In the two billiard gas models just discussed there is no local therm alequilibrium. Even though the internal temperature can be clearly de ned at any position [8], the above property may be considered unsatisfactory [19]. In order to overcome this problem, we have recently introduced a similar model which however exhibits local therm alequilibrium, normaldi usion, and zero Lyapunov exponent [12].



F ig. 4. The geom etry of the alternate m ass-core hard potential channel. The elem entary cell is indicated by the two dotted lines. The bars have m ass M = 1, and the particles have m ass m = ($\overline{5}$ 1)=2. The two heat baths at tem peratures T_L and T_R are indicated.

This model consists of a one-dimensional chain of elastically colliding particles with alternate masses m and M. In order to prevent total momentum conservation we con ne the motion of particles of mass M. (bars) inside separate cells. Schematically the model is shown in Fig.4: particles with mass m move horizontally and collide with bars of mass M. which, besides suering collisions with the particles, are elastically rejected back at the edges of their cells. In between collisions, particles and bars move freely.

Numerical results[12] clearly indicate that this model also obeys the Fourier law.

3 A nom alous H eat C onduction

Numerical experiments have shown that in many one dimensional systems with total momentum conservation, the heat conduction does not obey the

Fourier law and the heat conductivity depends on the system size. For example, in the so-called FPU model, L, with = 2=5, and if the transverse motion is introduced, = 1=3. Moreover, in the billiard gas channels (with conserved total momentum), the value of diers from model to model[5]. The question is whether one can relate to the dynamical and statistical properties of the system.

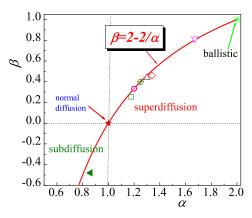


Fig. 5. Comparison of prediction (4) with numerical data. Normal di usion (?). The ballistic motion (). Superdi usion: 1D Ehrenfest gas channel[9](5); the rational triangle channel[11] (empty box); the polygonal billiard channel with $_1=(5\ 1)\ =4)$, and $_2==3\ [10](4)$; the triangle-square channel gas[6](). values are obtained from system size L 2 [192;384] for all channels except Ehrenfest channel[9]. The FPU lattice model at high temperature regime[6](), and the single walled nanotubes at room temperature (). Subdi usion: model from Ref.[10] (solid left triangle). The solid curve is $=2\ 2=$.

Recently, a sim ple form ula has been found [5] which connects anom alous heat conductivity with anom alous disciplined usion. More precisely, it has been shown that for a one dimensional system, if the energy disciplined by

$$h^2 i = 2D t$$
; (0 < 2)

then the heat conductivity is given by

$$= j=rT/L$$
 (3)

where the exponent is

$$= 2 2 = :$$
 (4)

This relation connects heat conduction and di usion, quantitatively. As expected, normal di usion (= 1) corresponds to the size-independent

(= 0) heat conduction obeying the Fourier law .M oreover, a ballistic motion (= 2) implies that the thermal conductivity is proportional to the system size L, a superdi usive behavior (1 < < 2) implies a divergent thermal conductivity (> 0), and a subdi usive behavior (< 1) implies zero thermal conductivity (< 0) in the thermodynamic limit.

The simple relation (4) is in good agreement with existing data from billiard gas channels to nonlinear lattices, and even single walled nanotubes[6]. This is shown in Fig. 5, where we compare the theoretical prediction (4) with existing data in dierent models.

We should mention here the one dimensional hard point gas model for which anomalous heat conduction has been found by several authors [20, 21]. However it seems there is no agreement on the numerical value of the exponent. Indeed in Ref.[20], the value 0.25 has been found, while the value 0.33 is reported in [21].

4 Control of heat ow

While in the previous sections we have discussed the relation between dynamical chaos and heat conductivity, in the following we will turn our attention to the possibility to control heat ow. A ctually a model of them all rectienthas been recently proposed [13] in which the heat can ow preferentially in one direction. Although this model is far away from a prototype realization, it is based on a mechanism of very general nature and, as such, is suitable of improvement and may eventually lead to real applications. This problem is discussed in the next section.

4.1 Therm aldiode

In a recent paper [14], a therm aldiodem odelhas been proposed in which, even though the underlying physical mechanism is similar to the one in Ref.[13], there is a new crucial element which allows to improve the eciency by more than two orders of magnitude.

The diode model consists of two segments of nonlinear lattices coupled together by a harm onic spring with constant strength $k_{\rm int}$ (see Fig. 6). Each segment is described by the (dimensionless) Hamiltonian:

$$H = \frac{X}{2m} + \frac{p_i^2}{2k} + \frac{1}{2k} (x_i \quad x_{i+1} \quad a)^2 \quad \frac{V}{(2)^2} \cos 2 x_i;$$
 (5)

The two ends of the system are put into contact with them albaths at tem perature T_L and T_R for left and right bath, respectively. In fact, Eq. (5) is the H am iltonian of the Frenkel-K ontorova (FK) model which is known to have norm alheat conduction [23]. For simplicity we set the mass of the particles and the lattice constant m=a=1. Thus the adjustable parameters are

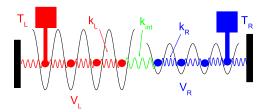
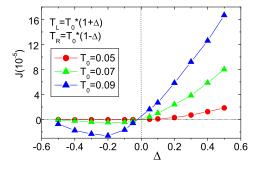


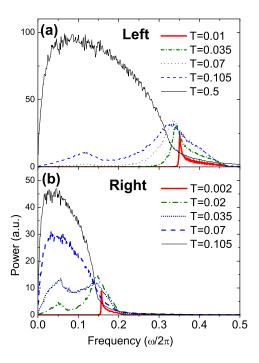
Fig. 6.Con guration of the therm aldiode model based on two coupled FK chains.

 $\langle k_L\;;k_{\rm int};k_R\;;V_L\;;V_R\;;T_L\;;T_R\;\rangle$, where the letter L/R indicates the left/right segment. In order to reduce the number of adjustable parameters, we set $V_R=V_L$, $k_R=k_L$, $T_L=T_0\,(l+\;);T_R=T_0\,(l\;)$ and, unless otherwise stated, we $x\;V_L=5$, $k_L=1$ so that the adjustable parameters are reduced to four, (; ;k $_{\rm int};T_0$). Notice that when >0, the left bath is at higher temperature and vice versa when <0.

In Fig. 7 we plot the heat current J versus—for di—erent tem peratures T_0 . It is clearly seen that when > 0 the heat current (J_+) increases with , while in the region < 0 the heat current (J_-) is almost zero, i.e. the system behaves as a therm alinsulator. The results in Fig. 7 show that our model has the rectifying e—ect in a wide range of tem peratures. The rectifying e—ciency, de—ned as $jI_-=J_-$ j could be as high as few hundreds times, depending on tem perature as well as on other parameters.



F ig.7.H eat current J versus the dim ensionless tem perature di erence for di erent values of T_0 . H ere the total num ber of particles N=100, $k_{\rm int}=0.05$, =0.2. The lines are drawn to guide the eye.



F ig. 8. Spectra of the two particles at the interface for di erent tem peratures at $k_{\text{int}} = 0$. (a) particle at the left side of the interface, (b) particle at the right side of the interface. Here = 0.2, N = 100.

Rectifying mechanism

To understand the underlying rectifying mechanism, let's start from the energy spectrum of the interface particles. Fig. 8 shows the phonon spectra of the left and right interface particles at dierent temperature when the two lattices are decoupled ($k_{\rm int}=0$).

The m atch/m ism atch of the energy spectra of the two interface particles controls the heat current. It is clearly seen from Fig. 8 that, if the left end is in contact with the high temperature bath $T_{\rm L}$, and the right end with the low temperature bath $T_{\rm R}$ (< $T_{\rm L}$), then the phonon spectra of the two particles at interface overlap in a large range of frequencies, thus the heat current can easily go through the system from the left end to the right end. However, if the left end is at lower temperature $T_{\rm L}$ and the right end is at higher temperature $T_{\rm R}$ (> $T_{\rm L}$), then the phonon spectrum of the right interface particle is mainly in the low frequency part, while the left interface particle is in the high frequency part. Then there is almost no overlap in phonon frequency, and the heat current can hardly go through from right to

left, and the system behaves as an insulator. Why the left and right particles at the interface have so dierent phonon spectra? This can be understood from the following analysis on temperature dependent phonon spectra, due to the nonlinearity.

(1) Low tem perature lim it. At low tem perature, the particle is con ned in the valley of the on-site potential. By linearizing the equation of motion one can easily obtain the frequency band [14]:

$$p_{\overline{V}} < ! < p_{\overline{V} + 4k}; \tag{6}$$

For the case of Fig. 7 w ith T = 0.01 (left) and T = 0.002 (right), this corresponds to 0.36 < !=2 < 0.48 for the left particle and to 0.16 < !=2 < 0.21 for the right particle.

As the tem perature is increased, the interparticle potential $kx^2=2$ becomes more and more important until a critical value $T_{\rm cr} = V=(2)^2$ is reached (we take the Boltzman constant equal unity), when the kinetic energy is large enough to overcome the on-site potential barrier. At this point low frequency appears and this happens at the critical temperatures $T_{\rm cr}=0.13$ for V=5 (left), and $T_{\rm cr}=0.025$ for V=1 (right). This is in quite good agreement with the data of Fig.8.

(2) High temperature limit. In the high temperature limit the on-site potential can be neglected, the system is close to two coupled harmonic chains, and the phonon band is is given by [24]:

$$0 < ! < 2 k;$$
 (7)

which gives 0 < !=2 < 0.32 for the left particle and 0 < !=2 < 0.14 for the right particle, again in good agreem ent with Fig.8.

In fact, in order to optim ize the rectifying e ect, one should avoid the overlapping of the phonon bands in the low temperature \lim it (Eq.6) and that in the high temperature \lim it (Eq.7) for each segment of the system . A coording to the above estimates, one should have V > 4k, which is satisfied for the case of Fig.8.

We should stress that it is the nonlinearity of the potential that makes phonon spectra temperature dependent, and thus the rectifying elect possible. Therefore it is reasonable to expect the rectifying elect to be present, in dierent degrees, in typical nonlinear lattices.

4.2 Negative Di erential Therm al Conductance

Apart from the \one-way heat ow ", the negative di erential therm al resistance phenom enon observed in a certain tem perature intervals in the therm al diode is of particular interest. As illustrated in Fig.7 for < 0.2, a sm aller tem perature di erence (), can induce a larger heat current since, due to nonlinearity, it can result in a better m atch in phonon bands.

The same phenomenon is shown for dierent inter-face coupling constants k_{int} in Fig. 9(a), and dierent system size in Fig. 9(b).

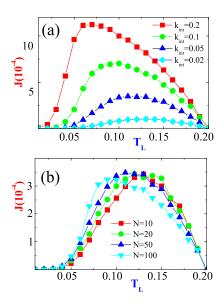


Fig. 9. (a) Heat current versus temperature T_L (at xed $T_R=0.2$) for dierent coupling constants, $k_{\rm int}$, with lattice size N=50. The system parameters are: $V_L=5$, $V_R=1$, $k_L=1$, $k_R=0.2$. (b) Same as (a) but for dierent system size N. $k_{\rm int}=0.05$. Notice that when $T_L=0.1$ the heat current increases with decreasing the external temperature dierence.

4.3 Therm al Transistor

The phenom enon of negative di erential therm al resistance allow sus to propose a \them altransistor" [15]. The con guration of the them altransistor is shown in Fig.10(a). It consists of three segments, D, S and G. The names D, S and G follow the ones used in a MOSFET (Metal-Oxide-Semiconductor Field-E ect-Transistor) that is the most important device for very large scale integrated chips such as microprocessors and semiconductor memories. Segment D (from D to O) has a negative di erential thermal resistance in a certain tem perature regim e while segment S is a norm alheat conductor, i.e., heat current inside this segment is positively dependent on temperature difference. Segment G is the control segment, which is connected to the junction particle between segments S and D . Tem perature $T_{\text{G}}\$ will be used to control tem perature T_{\circ} (at the junction 0) so as to control the heat current from D to S. In analogy to the MOSFET, in which the electronic current in the electrode G is very sm all, we require here that the heat current J_G through segment G to be as small as possible, (otherwise it is hard to set T_{G} to a required value in experim ent). M oreover the heat resistance of segm ent G must

be sm allenough in order to well control the tem perature T_{o} by changing T_{G} so that $T_{\text{o}}-T_{\text{G}}$.

Notice that, in typical situations, the dierential heat resistance, $R_S=\frac{\frac{\theta \ J_S}{\theta \ T_O}}{T_S=const}$ in segment S, and $R_D=\frac{\frac{\theta \ J_D}{\theta \ T_O}}{\theta \ T_O}$ in segment D, are both positive and therefore there exists only one value of T_O for which $J_S=J_D$ so that $J_G=0$, Since $J_S=J_D+J_G$, the \current amplication factor", $=\frac{\theta \ J_D}{\theta \ J_G}=\frac{R_S}{R_S+R_D}<1$; namely in order to make a change $\ J_D$, the control heat bath has to provide a larger $\ J_G$. This means that the \transistor" can never work!

The key point of our transistor model is the \negative di erential heat resistance" as we observed in the diode model[14]. It provides the possibility that when $T_{\rm o}$ changes both $J_{\rm S}$ and $J_{\rm D}$ change simultaneously in the same way. Therefore $J_{\rm S}=J_{\rm D}$ (or $J_{\rm S}-J_{\rm D}$) can be achieved for several di erent values of $T_{\rm o}$ or even in a wide region of $T_{\rm o}$ as shown in Figs.10 and 11. In this situation heat switch and heat modulator/ampli er are possible. In the ideal, limiting case of $R_{\rm S}=R_{\rm D}$ which, in principle, can be obtained by adjusting parameters, the transistor works perfectly.

Them alswitch

We rst dem onstrate the \sw itch" function of our transistor, namely we show that the system can act like a good heat conductor or an insulator depending on the control tem perature. This is illustrated in Fig.10 (b), where we plot $J_{\rm G}$; $J_{\rm S}$, and $J_{\rm D}$ versus $T_{\rm G}$. When $T_{\rm G}$ increases from 0.03 to 0:135, both $J_{\rm D}$ and $J_{\rm S}$ increase. In particular, at three points: $T_{\rm G}$ 0.04;0.09 and 0:135; $J_{\rm D}=J_{\rm S}$ thus $J_{\rm G}$ is exactly zero. These three points correspond to \o ",\sem i-on" and \on" states, at which $J_{\rm D}$ is 2:4 $\,$ 10 6 ;1.2 $\,$ 10 4 and 2:3 $\,$ 10 4 , respectively. The ratio of the heat current at the \on" state and that at the \o " state is about 100, hence our model displays one in portant function - sw itch - just like the function of a M O SFET used in a digital circuit.

Therm alm odulator/am pli er

As demonstrated above, the heat current from D to S can be switched between di erent values. However, in many cases, like in an analog circuit, we need to continuously adjust the current $J_{\rm S}$ and/or $J_{\rm D}$ in a wide range by adjusting the control temperature $T_{\rm G}$. In Fig.11 we demonstrate this \modulator/ampli er" function of our transistor. The basic mechanism of such \modulator/ampli er" is the same as that of the \switch" but we consider here di erent parameter values. It is seen that in the temperature interval $T_{\rm G}$ 2 (0.05;0:135), the heat current through the segment G remains very small ((10 5 10 5), within the shadow strip in Fig.10, while the heat currents $J_{\rm S}$ and $J_{\rm G}$ continuously increase from 5 10 5 to 2 10 4 .

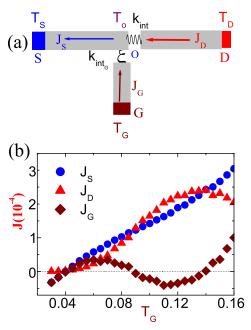


Fig. 10. (a) C on guration of the therm all transistor. (b) Heat current versus the control tem perature T_{G} . Param eters are: $T_{\text{D}}=0.2; V_{\text{D}}=1.0; k_{\text{D}}=0.2; k_{\text{int}}=0.05; T_{\text{S}}=0.04; V_{\text{S}}=5; k_{\text{S}}=0.2; V_{\text{G}}=5; k_{\text{G}}=1; k_{\text{int}_{\text{G}}}=1.\, \text{N otice}$ that both J_{S} and J_{D} increase when the tem perature T_{G} is increased.

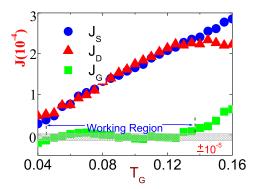


Fig. 11. Heat current versus the control tem perature T_G . Here: $T_D=0.2$; $V_D=1.0$; $k_D=0.2$; $T_S=0.04$; $V_S=5$; $k_S=0.2$; $k_{\rm int}=0.05$; $V_G=5$; $k_G=1$; $k_{\rm int}$ = 0.1. The shadow region is the range of variation of J_G in the tem perature interval $T_G=2$ (0.05;0:135).

5 Conclusions and discussions

In this paper, we have given a brief sum mary of our recent work on heat conduction in one dimensional systems. We have shown that strong chaos is su cient but not strictly necessary for the validity of the Fourier heat law. Indeed linear mixing can be su cient to induce a di usive process which ensures normal heat conductivity.

For system s with totalm omentum conservation one typically nds anom alous conductivity, namely the thermal conductivity is divergent with the system size. A nomalous conductivity has been connected with anomalous diusion via the very simple formula (4).

Finally we have shown the possibility to build a thermal diode which exhibits a very signicant rectifying elect in a very wide range of system param eters. Moreover, based on the phenomienon of negative differential thermal resistance observed in the thermal diode, we have built a theoretical model for a thermal transistor. The model displays two basic functions of a transistor: switch and modulator/amplier. Although at present it is just a model we believe that, sooner or later, it can be realized in a nanoscale system experiment. After all the Frenkel-Kontorova model used in our simulation is a very popular model in condensed matter physics [25].

A cknow ledgem ent

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